

680x680um Silicon PD Chip datasheet

P/N : WS95-01C

Feature

Si PIN photodiode chip

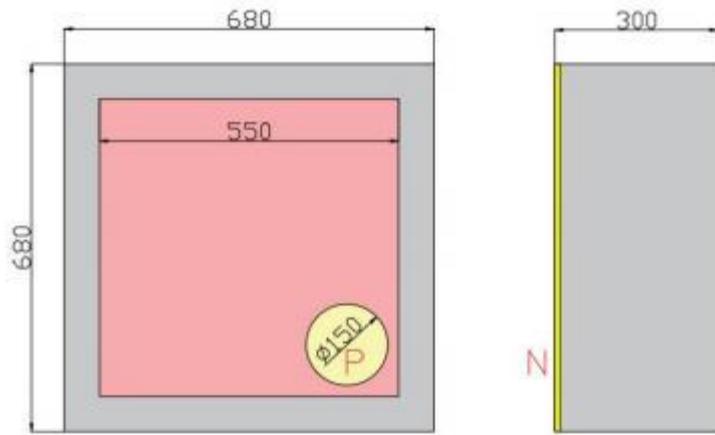
Structure

Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au

Top side (Anode) : Al



DIMENSIONS

Conditions	Min.	Typ.	Max.	Unit
Active	550x 550± 15			μm
Chip width	680±40			μm
Chip length	680±40			μm
Chip height	280	300	320	μm
Pad Area	140	150	160	μm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA	60			V
Reverse Dark Current	Id	Vr=10V			10	nA
Reverse light Current	IL	01V, 1 mW/cm2 @660nm	0.4			uA
Sensitive Wavelength Range	λ		430		1100	nm
Capacitance	Cj	VR=3V, H=0, F=1MHz		9		pF